

Francisco Gamiz

List of Publications by Year in descending order

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372
papers

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117571

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53
g-index

384
all docs

384
docs citations

384
times ranked

2486
citing authors

#	ARTICLE	IF	CITATIONS
1	On the enhanced electron mobility in strained-silicon inversion layers. Journal of Applied Physics, 2002, 92, 7320-7324.	1.1	215
2	Monte Carlo simulation of double-gate silicon-on-insulator inversion layers: The role of volume inversion. Journal of Applied Physics, 2001, 89, 5478-5487.	1.1	142
3	Electron transport in strained Si inversion layers grown on SiGe-on-insulator substrates. Journal of Applied Physics, 2002, 92, 288-295.	1.1	141
4	Surface roughness at the Si/SiO ₂ interfaces in fully depleted silicon-on-insulator inversion layers. Journal of Applied Physics, 1999, 86, 6854-6863.	1.1	106
5	Mechanical and thermal properties of graphene modified asphalt binders. Construction and Building Materials, 2018, 180, 265-274.	3.2	101
6	Physical model for trap-assisted inelastic tunneling in metal-oxide-semiconductor structures. Journal of Applied Physics, 2001, 90, 3396-3404.	1.1	89
7	A comprehensive model for Coulomb scattering in inversion layers. Journal of Applied Physics, 1994, 75, 924-934.	1.1	83
8	Direct and trap-assisted elastic tunneling through ultrathin gate oxides. Journal of Applied Physics, 2002, 91, 5116-5124.	1.1	77
9	Modeling the Centroid and the Inversion Charge in Cylindrical Surrounding Gate MOSFETs, Including Quantum Effects. IEEE Transactions on Electron Devices, 2008, 55, 411-416.	1.6	76
10	A Comprehensive Study of the Corner Effects in Pi-Gate MOSFETs Including Quantum Effects. IEEE Transactions on Electron Devices, 2007, 54, 3369-3377.	1.6	75
11	Monte Carlo simulation of electron transport properties in extremely thin SOI MOSFET's. IEEE Transactions on Electron Devices, 1998, 45, 1122-1126.	1.6	74
12	Acoustic phonon confinement in silicon nanolayers: Effect on electron mobility. Journal of Applied Physics, 2006, 100, 013701.	1.1	73
13	Effects of the inversion-layer centroid on the performance of double-gate MOSFETs. IEEE Transactions on Electron Devices, 2000, 47, 141-146.	1.6	72
14	Effects of the inversion layer centroid on MOSFET behavior. IEEE Transactions on Electron Devices, 1997, 44, 1915-1922.	1.6	67
15	Universality of electron mobility curves in MOSFETs: a Monte Carlo study. IEEE Transactions on Electron Devices, 1995, 42, 258-265.	1.6	62
16	An in-depth simulation study of thermal reset transitions in resistive switching memories. Journal of Applied Physics, 2013, 114, .	1.1	58
17	A simple subthreshold swing model for short channel MOSFETs. Solid-State Electronics, 2001, 45, 391-397.	0.8	56
18	A Monte Carlo study on the electron transport properties of high-performance strained Si on relaxed Si _{1-x} Ge _x channel MOSFETs. Journal of Applied Physics, 1996, 80, 5121-5128.	1.1	54

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19	Modeling effects of electron-velocity overshoot in a MOSFET. IEEE Transactions on Electron Devices, 1997, 44, 841-846.	1.6	53
20	Role of surface-roughness scattering in double gate silicon-on-insulator inversion layers. Journal of Applied Physics, 2001, 89, 1764.	1.1	48
21	Experimental Demonstration of Capacitorless A2RAM Cells on Silicon-on-Insulator. IEEE Electron Device Letters, 2012, 33, 1717-1719.	2.2	48
22	Electron mobility in extremely thin single-gate silicon-on-insulator inversion layers. Journal of Applied Physics, 1999, 86, 6269-6275.	1.1	46
23	Remote Coulomb scattering in metal-oxide-semiconductor field effect transistors: Screening by electrons in the gate. Applied Physics Letters, 2003, 83, 4848-4850.	1.5	46
24	Novel Capacitorless 1T-DRAM Cell for 22-nm Node Compatible With Bulk and SOI Substrates. IEEE Transactions on Electron Devices, 2011, 58, 2371-2377.	1.6	46
25	Reconfigurable Distributed Network Control System for Industrial Plant Automation. IEEE Transactions on Industrial Electronics, 2004, 51, 1168-1180.	5.2	45
26	Multi-Subband Monte Carlo study of device orientation effects in ultra-short channel DGSOI. Solid-State Electronics, 2010, 54, 131-136.	0.8	43
27	A-RAM Memory Cell: Concept and Operation. IEEE Electron Device Letters, 2010, 31, 972-974.	2.2	42
28	Monte Carlo simulation of remote-Coulomb-scattering-limited mobility in metal-oxide-semiconductor transistors. Applied Physics Letters, 2003, 82, 3251-3253.	1.5	41
29	A Simple Approach to Quantum Confinement in Tunneling Field-Effect Transistors. IEEE Electron Device Letters, 2012, 33, 1342-1344.	2.2	39
30	Impact of Quantum Confinement on Gate Threshold Voltage and Subthreshold Swings in Double-Gate Tunnel FETs. IEEE Transactions on Electron Devices, 2012, 59, 3205-3211.	1.6	38
31	Assessment of field-induced quantum confinement in heterogate germanium electron-hole bilayer tunnel field-effect transistor. Applied Physics Letters, 2014, 105, 082108.	1.5	38
32	A model for the quantized accumulation layer in metal-insulator-semiconductor structures. Solid-State Electronics, 1995, 38, 203-210.	0.8	37
33	Influence of acoustic phonon confinement on electron mobility in ultrathin silicon on insulator layers. Applied Physics Letters, 2006, 88, 122108.	1.5	36
34	Revisited Pseudo-MOSFET Models for the Characterization of Ultrathin SOI Wafers. IEEE Transactions on Electron Devices, 2009, 56, 1507-1515.	1.6	36
35	A review of the Z ² -FET 1T-DRAM memory: Operation mechanisms and key parameters. Solid-State Electronics, 2018, 143, 10-19.	0.8	36
36	The dependence of the electron mobility on the longitudinal electric field in MOSFETs. Semiconductor Science and Technology, 1997, 12, 321-330.	1.0	34

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37	Scattering of electrons in silicon inversion layers by remote surface roughness. Journal of Applied Physics, 2003, 94, 392-399.	1.1	34
38	Extended Analysis of the Z^2 -FET: Operation as Capacitorless eDRAM. IEEE Transactions on Electron Devices, 2017, 64, 4486-4491.	1.6	34
39	Modeling the equivalent oxide thickness of Surrounding Gate SOI devices with high- ϵ insulators. Solid-State Electronics, 2008, 52, 1854-1860.	0.8	33
40	Why the Universal Mobility Is Not. IEEE Transactions on Electron Devices, 2010, 57, 1327-1333.	1.6	33
41	Electron mobility in double gate silicon on insulator transistors: Symmetric-gate versus asymmetric-gate configuration. Journal of Applied Physics, 2003, 94, 5732-5741.	1.1	32
42	Coulomb scattering in strained silicon inversion layers on Si $_{1-x}$ Ge $_x$ substrates. Applied Physics Letters, 1996, 69, 797-799.	1.5	31
43	An Analytical S^2 Model for Surrounding-Gate Transistors That Includes Quantum and Velocity Overshoot Effects. IEEE Transactions on Electron Devices, 2010, 57, 2925-2933.	1.6	30
44	Phonon-limited electron mobility in ultrathin silicon-on-insulator inversion layers. Journal of Applied Physics, 1998, 83, 4802-4806.	1.1	29
45	The Multivalley Effective Conduction Band-Edge Method for Monte Carlo Simulation of Nanoscale Structures. IEEE Transactions on Electron Devices, 2006, 53, 2703-2710.	1.6	29
46	Intra-amygdala ZIP injections impair the memory of learned active avoidance responses and attenuate conditioned taste-aversion acquisition in rats. Learning and Memory, 2011, 18, 529-533.	0.5	29
47	Metamaterial-Based Reconfigurable Intelligent Surface: 3D Meta-Atoms Controlled by Graphene Structures. IEEE Communications Magazine, 2021, 59, 42-48.	4.9	29
48	Equivalent Oxide Thickness of Trigate SOI MOSFETs With High- κ Insulators. IEEE Transactions on Electron Devices, 2009, 56, 2711-2719.	1.6	28
49	An analytical model for square GAA MOSFETs including quantum effects. Solid-State Electronics, 2010, 54, 1463-1469.	0.8	28
50	Z^2 -FET as Capacitor-Less eDRAM Cell For High-Density Integration. IEEE Transactions on Electron Devices, 2017, 64, 4904-4909.	1.6	28
51	Impact of Asymmetric Configurations on the Heterogate Germanium Electron–Hole Bilayer Tunnel FET Including Quantum Confinement. IEEE Transactions on Electron Devices, 2015, 62, 3560-3566.	1.6	27
52	Capacitor-less dynamic random access memory based on a $3V$ transistor with a gate length of 14 nm. Nature Electronics, 2019, 2, 412-419.	13.1	27
53	Effects of nonparabolic bands in quantum wires. Journal of Applied Physics, 2005, 98, 013702.	1.1	24
54	Coulomb scattering model for ultrathin silicon-on-insulator inversion layers. Applied Physics Letters, 2002, 80, 3835-3837.	1.5	23

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55	Evidence for mobility enhancement in double-gate silicon-on-insulator metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2007, 102, 083712.	1.1	23
56	Hole effective mass in silicon inversion layers with different substrate orientations and channel directions. Journal of Applied Physics, 2011, 110, .	1.1	23
57	Analytic potential and charge model for III-V surrounding gate metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2012, 112, .	1.1	23
58	Reaching sub-32nm nodes: ET-FDSOI and BOX optimization. Solid-State Electronics, 2012, 70, 101-105.	0.8	23
59	On the extension of ET-FDSOI roadmap for 22nm node and beyond. Solid-State Electronics, 2013, 90, 23-27.	0.8	23
60	Study of the effects of a stepped doping profile in short-channel MOSFETs. IEEE Transactions on Electron Devices, 1997, 44, 1425-1431.	1.6	22
61	A model for the drain current of deep submicrometer MOSFETs including electron-velocity overshoot. IEEE Transactions on Electron Devices, 1998, 45, 2249-2251.	1.6	22
62	Surface roughness scattering model for arbitrarily oriented silicon nanowires. Journal of Applied Physics, 2011, 110, 084514.	1.1	22
63	On the gate capacitance limits of nanoscale DG and FD SOI MOSFETs. IEEE Transactions on Electron Devices, 2006, 53, 753-758.	1.6	21
64	Modeling of Inversion Layer Centroid and Polysilicon Depletion Effects on Ultrathin-Gate-Oxide MOSFET Behavior: The Influence of Crystallographic Orientation. IEEE Transactions on Electron Devices, 2007, 54, 723-732.	1.6	21
65	Experimental Demonstration of Operational Z^{2} -FET Memory Matrix. IEEE Electron Device Letters, 2018, 39, 660-663.	2.2	21
66	Hole Mobility in Ultrathin Double-Gate SOI Devices: The Effect of Acoustic Phonon Confinement. IEEE Electron Device Letters, 2009, 30, 1338-1340.	2.2	20
67	Simulation of hole mobility in two-dimensional systems. Semiconductor Science and Technology, 2009, 24, 035016.	1.0	20
68	Confinement-induced InAs/GaSb heterojunction electronâ€“hole bilayer tunneling field-effect transistor. Applied Physics Letters, 2018, 112, .	1.5	20
69	Effects of oxide-charge space correlation on electron mobility in inversion layers. Semiconductor Science and Technology, 1994, 9, 1102-1107.	1.0	19
70	A comparison of models for phonon scattering in silicon inversion layers. Journal of Applied Physics, 1995, 77, 4128-4129.	1.1	18
71	Strained-Si on Si/sub 1-x/ mosfet mobility model. IEEE Transactions on Electron Devices, 2003, 50, 1408-1411.	1.6	18
72	Hole transport in DGSOI devices: Orientation and silicon thickness effects. Solid-State Electronics, 2010, 54, 191-195.	0.8	18

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73	Multi-Subband Ensemble Monte Carlo simulation of bulk MOSFETs for the 32nm-node and beyond. Solid-State Electronics, 2011, 65-66, 88-93.	0.8	18
74	Spontaneous object recognition memory in aged rats: Complexity versus similarity. Learning and Memory, 2012, 19, 444-448.	0.5	18
75	Analytical Gate Capacitance Modeling of III-V Nanowire Transistors. IEEE Transactions on Electron Devices, 2013, 60, 1590-1599.	1.6	18
76	Experimental developments of A2RAM memory cells on SOI and bulk substrates. Solid-State Electronics, 2015, 103, 7-14.	0.8	18
77	Electron mobility in ultrathin silicon-on-insulator layers at 4.2 K. Applied Physics Letters, 2004, 84, 2298-2300.	1.5	17
78	Implications of nonparabolicity, warping, and inelastic phonon scattering on hole transport in pure Si and Ge within the effective mass framework. Journal of Applied Physics, 2005, 97, 013702.	1.1	17
79	Quantum-mechanical effects in multiple-gate MOSFETs. Journal of Computational Electronics, 2007, 6, 145-148.	1.3	17
80	Simulation of Fabricated 20-nm Schottky Barrier MOSFETs on SOI: Impact of Barrier Lowering. IEEE Transactions on Electron Devices, 2012, 59, 1320-1327.	1.6	17
81	Electrical characterization of Random Telegraph Noise in Fully-Depleted Silicon-On-Insulator MOSFETs under extended temperature range and back-bias operation. Solid-State Electronics, 2016, 117, 60-65.	0.8	17
82	Multibranch Mobility Analysis for the Characterization of FDSOI Transistors. IEEE Electron Device Letters, 2012, 33, 1102-1104.	2.2	16
83	Electrical characterization and conductivity optimization of laser reduced graphene oxide on insulator using point-contact methods. RSC Advances, 2016, 6, 46231-46237.	1.7	16
84	Influence of the oxide-charge distribution profile on electron mobility in MOSFET's. IEEE Transactions on Electron Devices, 1995, 42, 999-1004.	1.6	15
85	Influence of mobility fluctuations on random telegraph signal amplitude in n-channel metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 1997, 82, 4621-4628.	1.1	15
86	Calculation of the phonon-limited mobility in silicon Gate All-Around MOSFETs. Solid-State Electronics, 2007, 51, 1211-1215.	0.8	15
87	A new characterization technique for SOI wafers: Split C(V) in pseudo-MOSFET configuration. Solid-State Electronics, 2013, 90, 127-133.	0.8	15
88	Low-Power Z2-FET Capacitorless 1T-DRAM. , 2017, , .		15
89	An analytical expression for phonon-limited electron mobility in silicon inversion layers. Journal of Applied Physics, 1993, 74, 3289-3292.	1.1	14
90	Density of states of a two-dimensional electron gas including nonparabolicity. Journal of Applied Physics, 1994, 75, 4267-4269.	1.1	14

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91	Oxide charge space correlation in inversion layers. II. Three-dimensional oxide charge distribution. Semiconductor Science and Technology, 1995, 10, 592-600.	1.0	14
92	Deep submicrometer SOI MOSFET drain current model including series resistance, self-heating and velocity overshoot effects. IEEE Electron Device Letters, 2000, 21, 239-241.	2.2	14
93	Temperature behaviour of electron mobility in double-gate silicon on insulator transistors. Semiconductor Science and Technology, 2004, 19, 113-119.	1.0	14
94	Influence of Orientation, Geometry, and Strain on Electron Distribution in Silicon Gate-All-Around (GAA) MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 3350-3357.	1.6	14
95	Two-Dimensional Monte Carlo Simulation of DGSOI MOSFET Misalignment. IEEE Transactions on Electron Devices, 2012, 59, 1621-1628.	1.6	14
96	Bias-Engineered Mobility in Advanced FD-SOI MOSFETs. IEEE Electron Device Letters, 2013, 34, 840-842.	2.2	14
97	The effect of quantum confinement on tunneling field-effect transistors with high- ϵ gate dielectric. Applied Physics Letters, 2013, 103, .	1.5	14
98	Assessment of pseudo-bilayer structures in the heterogate germanium electron-hole bilayer tunnel field-effect transistor. Applied Physics Letters, 2015, 106, .	1.5	14
99	Analytic drain current model for III-V cylindrical nanowire transistors. Journal of Applied Physics, 2015, 118, 044502.	1.1	14
100	Double gate silicon on insulator transistors. A Monte Carlo study. Solid-State Electronics, 2004, 48, 937-945.	0.8	13
101	Coulomb scattering in high- ϵ gate stack silicon-on-insulator metal-oxide-semiconductor field effect transistors. Journal of Applied Physics, 2008, 104, 063704.	1.1	13
102	Influence of the interface trap location on the performance and variability of ultra-scaled MOSFETs. Microelectronics Reliability, 2013, 53, 1243-1246.	0.9	13
103	Simulation study of the electron mobility in few-layer MoS ₂ metal-oxide-semiconductor field-effect transistors. Solid-State Electronics, 2015, 114, 30-34.	0.8	13
104	Investigating the transient response of Schottky barrier back-gated MoS ₂ transistors. 2D Materials, 2020, 7, 025040.	2.0	13
105	Influence of negatively and positively charged scattering centers on electron mobility in semiconductor inversion layers: A Monte Carlo study. Journal of Applied Physics, 1995, 78, 1787-1792.	1.1	12
106	Strained-Si on Si _{1-x} Ge _x MOSFET inversion layer centroid modeling. IEEE Transactions on Electron Devices, 2001, 48, 2447-2449.	1.6	12
107	Effect of polysilicon depletion charge on electron mobility in ultrathin oxide MOSFETs. Semiconductor Science and Technology, 2003, 18, 927-937.	1.0	12
108	Gate bias symmetry dependency of electron mobility and prospect of velocity modulation in double-gate silicon-on-insulator transistors. Applied Physics Letters, 2004, 85, 5442-5444.	1.5	12

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109	Simulation and modelling of transport properties in strained-Si and strained-Si/SiGe-on-insulator MOSFETs. Solid-State Electronics, 2004, 48, 1347-1355.	0.8	12
110	An Inversion-Charge Analytical Model for Square Gate-All-Around MOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 2854-2861.	1.6	12
111	Self-heating effects in ultrathin FD SOI transistors. , 2011, , .		12
112	Modeling the Channel Charge and Potential in Quasi-Ballistic Nanoscale Double-Gate MOSFETs. IEEE Transactions on Electron Devices, 2014, 61, 2640-2646.	1.6	12
113	Mobility and Capacitance Comparison in Scaled InGaAs Versus Si Trigate MOSFETs. IEEE Electron Device Letters, 2015, 36, 114-116.	2.2	12
114	Impact of the Back-Gate Biasing on Trigate MOSFET Electron Mobility. IEEE Transactions on Electron Devices, 2015, 62, 224-227.	1.6	12
115	Multisubband Ensemble Monte Carlo Analysis of Tunneling Leakage Mechanisms in Ultrascaled FDSOI, DGSOI, and FinFET Devices. IEEE Transactions on Electron Devices, 2019, 66, 1145-1152.	1.6	12
116	A procedure for the determination of the effective mobility in an N-MOSFET in the moderate inversion region. Solid-State Electronics, 1996, 39, 875-883.	0.8	11
117	A Model of the Gate Capacitance of Surrounding Gate Transistors: Comparison With Double-Gate MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 2477-2483.	1.6	11
118	Capacitor-less A-RAM SOI memory: Principles, scaling and expected performance. Solid-State Electronics, 2011, 59, 44-49.	0.8	11
119	Impact of back-gate biasing on effective field and mobility in ultrathin silicon-on-insulator metal-oxide-semiconductor field-effect-transistors. Journal of Applied Physics, 2013, 113, .	1.1	11
120	A parallel deterministic solver for the Schrödinger-Poisson-Boltzmann system in ultra-short DG-MOSFETs: Comparison with Monte-Carlo. Computers and Mathematics With Applications, 2014, 67, 1703-1721.	1.4	11
121	3D multi-subband ensemble Monte Carlo simulator of FinFETs and nanowire transistors. , 2014, , .		11
122	Ultra-low power 1T-DRAM in FDSOI technology. Microelectronic Engineering, 2017, 178, 245-249.	1.1	11
123	Source-to-Drain Tunneling Analysis in FDSOI, DGSOI, and FinFET Devices by Means of Multisubband Ensemble Monte Carlo. IEEE Transactions on Electron Devices, 2018, 65, 4740-4746.	1.6	11
124	Thorough Understanding of Retention Time of Z2FET Memory Operation. IEEE Transactions on Electron Devices, 2019, 66, 383-388.	1.6	11
125	Influence of the interface-state density on the electron mobility in silicon inversion layers. Journal of Electronic Materials, 1993, 22, 1159-1163.	1.0	10
126	Anisotropy of electron mobility in arbitrarily oriented FinFETs. , 2007, , .		10

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127	Monte Carlo simulation of Hall and magnetoresistance mobility in SOI devices. Solid-State Electronics, 2007, 51, 1216-1220.	0.8	10
128	Analytic Potential and Charge Model of Semiconductor Quantum Wells. IEEE Transactions on Electron Devices, 2015, 62, 4186-4191.	1.6	10
129	Reliability Study of Thin-Oxide Zero-Ionization, Zero-Swing FET 1T-DRAM Memory Cell. IEEE Electron Device Letters, 2019, 40, 1084-1087.	2.2	10
130	Random telegraph signal amplitude in submicron n-channel metal oxide semiconductor field effect transistors. Applied Physics Letters, 1997, 70, 2153-2155.	1.5	9
131	Electron transport properties of quantized silicon carbide inversion layers. Journal of Electronic Materials, 1997, 26, 203-207.	1.0	9
132	Monte Carlo simulation of electron mobility in silicon-on-insulator structures. Solid-State Electronics, 2002, 46, 1715-1721.	0.8	9
133	Modeling of retention time degradation due to inelastic trap-assisted tunneling in EEPROM devices. Microelectronics Reliability, 2003, 43, 1495-1500.	0.9	9
134	Three-interface pseudo-MOSFET models for the characterization of SOI wafers with ultrathin film and BOX. Microelectronic Engineering, 2011, 88, 1236-1239.	1.1	9
135	Compact drain-current model for reproducing advanced transport models in nanoscale double-gate MOSFETs. Semiconductor Science and Technology, 2011, 26, 095015.	1.0	9
136	Accurate Calculation of Gate Tunneling Current in Double-Gate and Single-Gate SOI MOSFETs Through Gate Dielectric Stacks. IEEE Transactions on Electron Devices, 2012, 59, 2589-2596.	1.6	9
137	Theoretical interpretation of the electron mobility behavior in InAs nanowires. Journal of Applied Physics, 2014, 116, 174505.	1.1	9
138	Implementation of Band-to-Band Tunneling Phenomena in a Multisubband Ensemble Monte Carlo Simulator: Application to Silicon TFETs. IEEE Transactions on Electron Devices, 2017, 64, 3084-3091.	1.6	9
139	MS-EMC vs. NEGF: A comparative study accounting for transport quantum corrections. , 2018, , .		9
140	InGaAs Capacitor-Less DRAM Cells TCAD Demonstration. IEEE Journal of the Electron Devices Society, 2018, 6, 884-892.	1.2	9
141	Electron velocity saturation in quantized silicon carbide inversion layers. Applied Physics Letters, 1996, 69, 2219-2221.	1.5	8
142	Electron transport in ultrathin double-gate SOI devices. Microelectronic Engineering, 2001, 59, 423-427.	1.1	8
143	An electron mobility model for ultra-thin gate-oxide MOSFETs including the contribution of remote scattering mechanisms. Semiconductor Science and Technology, 2007, 22, 348-353.	1.0	8
144	Effect of confined acoustic phonons on the electron mobility of rectangular nanowires. Applied Physics Letters, 2013, 103, .	1.5	8

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145	Multi-Subband Ensemble Monte Carlo simulation of Si nanowire MOSFETs. , 2015, , .		8
146	Competitive 1T-DRAM in 28 nm FDSOI technology for low-power embedded memory. , 2016, , .		8
147	MSDRAM, A2RAM and Z ² -FET performance benchmark for 1T-DRAM applications. , 2018, , .		8
148	Gate Leakage Tunneling Impact on the InAs/GaSb Heterojunction Electronâ€Hole Bilayer Tunneling Field-Effect Transistor. IEEE Transactions on Electron Devices, 2018, 65, 4679-4686.	1.6	8
149	3-D TCAD Study of the Implications of Channel Width and Interface States on FD-SOI Z ² -FETs. IEEE Transactions on Electron Devices, 2019, 66, 2513-2519.	1.6	8
150	Near-field scanning microwave microscope platform based on a coaxial cavity resonator for the characterization of semiconductor structures. Solid-State Electronics, 2019, 159, 150-156.	0.8	8
151	Simulation Perspectives of Sub-1V Single-Supply Z ² -FET 1T-DRAM Cells for Low-Power. IEEE Access, 2019, 7, 40279-40284.	2.6	8
152	Electron transport in silicon-on-insulator devices. Solid-State Electronics, 2001, 45, 613-620.	0.8	7
153	A compact QM-based mobility model for nanoscale ultra-thin-body CMOS devices. , 0, , .		7
154	The effect of surface roughness scattering on hole mobility in double gate silicon-on-insulator devices. Journal of Applied Physics, 2009, 106, 023705.	1.1	7
155	Inversion charge modeling in n-type and p-type Double-Gate MOSFETs including quantum effects: The role of crystallographic orientation. Solid-State Electronics, 2012, 67, 30-37.	0.8	7
156	Switching Behavior Constraint in the Heterogate Electronâ€Hole Bilayer Tunnel FET: The Combined Interplay Between Quantum Confinement Effects and Asymmetric Configurations. IEEE Transactions on Electron Devices, 2016, 63, 2570-2576.	1.6	7
157	2D-TCAD simulation on retention time of Z2FET for DRAM application. , 2017, , .		7
158	Evaluation of thin-oxide Z2-FET DRAM cell. , 2018, , .		7
159	Dual PN Source/Drain Reconfigurable FET for Fast and Low-Voltage Reprogrammable Logic. IEEE Access, 2020, 8, 132376-132381.	2.6	7
160	Quantum Enhancement of a S/D Tunneling Model in a 2D MS-EMC Nanodevice Simulator: NEGF Comparison and Impact of Effective Mass Variation. Micromachines, 2020, 11, 204.	1.4	7
161	Effects of bulk-impurity and interface-charge on the electron mobility in MOSFETs. Solid-State Electronics, 1995, 38, 611-614.	0.8	6
162	A theoretical interpretation of magnetoresistance mobility in silicon inversion layers. Journal of Applied Physics, 2007, 102, 013708.	1.1	6

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163	Phonon scattering in Si-based nanodevices. Solid-State Electronics, 2007, 51, 593-597.	0.8	6
164	Monte Carlo simulation of nanoelectronic devices. Journal of Computational Electronics, 2009, 8, 174-191.	1.3	6
165	In-Depth Study of Quantum Effects in SOI DG MOSFETs for Different Crystallographic Orientations. IEEE Transactions on Electron Devices, 2011, 58, 4438-4441.	1.6	6
166	Optimisation and parallelisation of a 2D MOSFET multi-subband ensemble Monte Carlo simulator. International Journal of High Performance Computing Applications, 2013, 27, 483-492.	2.4	6
167	Tunability of effective masses on MoS ₂ monolayers. Microelectronic Engineering, 2015, 147, 302-305.	1.1	6
168	Impact of S/D tunneling in ultrascaled devices, a Multi-Subband Ensemble Monte Carlo study. , 2015, , .		6
169	A new explicit and analytical model for square Gate-All-Around MOSFETs with rounded corners. Solid-State Electronics, 2015, 111, 180-187.	0.8	6
170	Assessment of confinement-induced band-to-band tunneling leakage in the FinEHBT FET. , 2016, , .		6
171	Simulation based DC and dynamic behaviour characterization of Z2FET. , 2017, , .		6
172	Electron trapping and detrapping in near-interfacial traps during Fowler-Nordheim tunneling injection at 77 K. Microelectronic Engineering, 1995, 28, 317-320.	1.1	5
173	Understanding the improved performance of strained channel MOSFETs. Semiconductor Science and Technology, 1997, 12, 1603-1608.	1.0	5
174	A Monte Carlo study on electron mobility in quantized cubic silicon carbide inversion layers. Journal of Applied Physics, 1997, 81, 6857-6865.	1.1	5
175	A closed-loop evaluation and validation of a method for determining the dependence of the electron mobility on the longitudinal-electric field in MOSFETs. IEEE Transactions on Electron Devices, 1997, 44, 1447-1453.	1.6	5
176	Influence of technological parameters on the behavior of the hole effective mass in SiGe structures. Journal of Applied Physics, 2000, 88, 1978-1982.	1.1	5
177	Improving strained-Si on Si/sub 1-x/Ge/sub x/ deep submicron MOSFETs performance by means of a stepped doping profile. IEEE Transactions on Electron Devices, 2001, 48, 1878-1884.	1.6	5
178	Strained-Si/SiGe-on-insulator inversion layers: The role of strained-Si layer thickness on electron mobility. Applied Physics Letters, 2002, 80, 4160-4162.	1.5	5
179	Mobility enhancement via volume inversion in double-gate MOSFETs. , 2003, , .		5
180	Remote surface roughness scattering in ultrathin-oxide MOSFETs. , 0, , .		5

#	ARTICLE	IF	CITATIONS
181	A comprehensive study of velocity overshoot effects in double gate silicon on insulator transistors. Semiconductor Science and Technology, 2004, 19, 393-398.	1.0	5
182	Velocity overshoot in ultrathin double-gate silicon-on-insulator transistors. Applied Physics Letters, 2004, 84, 299-301.	1.5	5
183	Electron mobility and magneto transport study of ultra-thin channel double-gate Si MOSFETs. Solid-State Electronics, 2005, 49, 1516-1521.	0.8	5
184	Monte Carlo simulation of double gate silicon on insulator devices operated as velocity modulation transistors. Applied Physics Letters, 2005, 86, 202115.	1.5	5
185	Simulation of the electrostatic and transport properties of 3D-stacked GAA silicon nanowire FETs. Solid-State Electronics, 2011, 59, 62-67.	0.8	5
186	An analytical mobility model for square Gate-All-Around MOSFETs. Solid-State Electronics, 2013, 90, 18-22.	0.8	5
187	Taste and olfactory status in a gourmand with a right amygdala lesion. Neurocase, 2014, 20, 421-433.	0.2	5
188	Determination of ad hoc deposited charge on bare SOI wafers. , 2015, , .		5
189	Confinement orientation effects in S/D tunneling. Solid-State Electronics, 2017, 128, 48-53.	0.8	5
190	Systematic method for electrical characterization of random telegraph noise in MOSFETs. Solid-State Electronics, 2017, 128, 115-120.	0.8	5
191	Active Radiation-Hardening Strategy in Bulk FinFETs. IEEE Access, 2020, 8, 201441-201449.	2.6	5
192	An analytical model for the electron velocity overshoot effects in strained-Si on Si/sub x/Ge/sub 1-x/ MOSFETs. IEEE Transactions on Electron Devices, 1998, 45, 993-995.	1.6	4
193	Accurate Deterministic Numerical Simulation of p-n Junctions. Journal of Computational Electronics, 2004, 3, 235-238.	1.3	4
194	Mobility issues in double-gate SOI MOSFETs: Characterization and analysis. , 2007, , .		4
195	The Quantization Impact of Accumulated Carriers in Silicide-Gated MOSFETs. IEEE Electron Device Letters, 2008, 29, 628-631.	2.2	4
196	A-RAM: Novel capacitor-less DRAM memory. , 2009, , .		4
197	Properties of 22nm node extremely-thin-SOI MOSFETs. , 2011, , .		4
198	Determination of Effective Capacitance Area for Pseudo-MOSFET Based Characterization of Bare SOI Wafers by Split-C(V) Measurements. ECS Transactions, 2013, 53, 209-217.	0.3	4

#	ARTICLE	IF	CITATIONS
199	TCAD simulation of interface traps related variability in bulk decananometer mosfets. , 2014, , .		4
200	Analytical temperature dependent model for nanoscale double-gate MOSFETs reproducing advanced transport models. Solid-State Electronics, 2014, 98, 2-6.	0.8	4
201	Comment on "Germanium electron-hole bilayer tunnel field-effect transistors with a symmetrically arranged double gate"™. Semiconductor Science and Technology, 2015, 30, 128001.	1.0	4
202	Capacitor-less memory: Advances and challenges. , 2016, , .		4
203	Assessment of gate leakage mechanism utilizing Multi-Subband Ensemble Monte Carlo. , 2017, , .		4
204	Analysis of the Heterogate Electron-Hole Bilayer Tunneling Field-Effect Transistor With Partially Doped Channels: Effects on Tunneling Distance Modulation and Occupancy Probabilities. IEEE Transactions on Electron Devices, 2018, 65, 339-346.	1.6	4
205	Multi-Subband Ensemble Monte Carlo simulations of scaled GAA MOSFETs. Solid-State Electronics, 2018, 143, 49-55.	0.8	4
206	Impact of electron effective mass variation on the performance of InAs/GaSb Electron-Hole Bilayer Tunneling Field-Effect Transistor. , 2018, , .		4
207	On the Low-Frequency Noise Characterization of $Z^{2²}$ -FET Devices. IEEE Access, 2019, 7, 42551-42556.	2.6	4
208	Memory Operations of Zero Impact Ionization, Zero Subthreshold Swing FET Matrix Without Selectors. IEEE Electron Device Letters, 2020, 41, 361-364.	2.2	4
209	Synthesis of graphene and other two-dimensional materials. , 2021, , 1-79.		4
210	Performance of FDSOI double-gate dual-doped reconfigurable FETs. Solid-State Electronics, 2022, 194, 108336.	0.8	4
211	Image and exchange-correlation effects in double gate silicon-on-insulator transistors. Microelectronic Engineering, 2004, 72, 374-378.	1.1	3
212	Accurate modeling of Metal/HfO ₂ /Si capacitors. Journal of Computational Electronics, 2008, 7, 155-158.	1.3	3
213	Mobility in Multigate MOSFETs. , 2008, , 191-256.		3
214	Fully self-consistent k · p solver and Monte Carlo simulator for hole inversion layers. , 2008, , .		3
215	An in-depth simulation study of Coulomb mobility in ultra-thin-body SOI MOSFETs. Semiconductor Science and Technology, 2010, 25, 055002.	1.0	3
216	New concepts for IT-DRAMs: Overcoming the scaling limits. , 2011, , .		3

#	ARTICLE	IF	CITATIONS
217	Ab initio validation of continuum models parametrizations for ultrascaled SOI interfaces. <i>Microelectronic Engineering</i> , 2013, 109, 286-289.	1.1	3
218	Influence of alloy disorder scattering on the hole mobility of SiGe nanowires. <i>Journal of Applied Physics</i> , 2014, 116, .	1.1	3
219	Analytical model for the threshold voltage of III-V nanowire transistors including quantum effects. <i>Solid-State Electronics</i> , 2014, 92, 28-34.	0.8	3
220	Threshold voltage and on-current Variability related to interface traps spatial distribution. , 2015, , .		3
221	The unexpected beneficial effect of the $\langle i \rangle L \langle /i \rangle$ -valley population on the electron mobility of GaAs nanowires. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	3
222	Quantum Mechanical Confinement in the Fin Electron-Hole Bilayer Tunnel Field-Effect Transistor. <i>IEEE Transactions on Electron Devices</i> , 2016, , 1-7.	1.6	3
223	Electrostatic performance of InSb, GaSb, Si and Ge p-channel nanowires. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 495106.	1.3	3
224	Multi-subband ensemble Monte Carlo study of tunneling leakage mechanisms. , 2017, , .		3
225	Towards InGaAs MSDRAM Capacitor-Less Cells. <i>ECS Transactions</i> , 2018, 85, 195-200.	0.3	3
226	Investigation of thin gate-stack Z2-FET devices as capacitor-less memory cells. <i>Solid-State Electronics</i> , 2019, 159, 12-18.	0.8	3
227	Hysteresis in As-Synthesized MoS2 Transistors: Origin and Sensing Perspectives. <i>Micromachines</i> , 2021, 12, 646.	1.4	3
228	Impact of the Trap Attributes on the Gate Leakage Mechanisms in a 2D MS-EMC Nanodevice Simulator. <i>Lecture Notes in Computer Science</i> , 2019, , 273-280.	1.0	3
229	A Review of Sharp-Switching Band-Modulation Devices. <i>Micromachines</i> , 2021, 12, 1540.	1.4	3
230	Influence of the doping profile on electron mobility in a MOSFET. <i>IEEE Transactions on Electron Devices</i> , 1996, 43, 2023-2025.	1.6	2
231	Influence of image force and many-body correction on electron mobility in ultrathin double gate silicon on insulator inversion layers. <i>Applied Physics Letters</i> , 2003, 83, 3120-3122.	1.5	2
232	A comprehensive study of carrier velocity modulation in DGSOI transistors. <i>Solid-State Electronics</i> , 2005, 49, 1504-1509.	0.8	2
233	Quantum Ensemble Monte Carlo simulation of silicon-based nanodevices. <i>Journal of Computational Electronics</i> , 2007, 6, 41-44.	1.3	2
234	Monte Carlo simulation of low-field mobility in strained double gate SOI transistors. <i>Journal of Computational Electronics</i> , 2008, 7, 205-208.	1.3	2

#	ARTICLE	IF	CITATIONS
235	Comparison of the Electrostatics of Bulk and SOI Trigate MOSFETs. ECS Transactions, 2009, 19, 127-132.	0.3	2
236	On the role of Coulomb scattering in hafnium-silicate gated silicon n and p-channel metal-oxide-semiconductor-field-effect-transistors. Journal of Applied Physics, 2011, 110, 124503.	1.1	2
237	Impact of effective capacitance area on the characterization of SOI Wafers by Split-C(V) in Pseudo-MOSFET configuration. , 2012, , .		2
238	A 20nm low-power triple-gate multibody 1T-DRAM cell. , 2012, , .		2
239	Two-band $k^{\circ}\hat{A}^{\circ}\rho$ model for Si-(110) electron devices. Journal of Applied Physics, 2013, 114, 073706.	1.1	2
240	An in-depth Monte Carlo study of low-field mobility in ultra-thin body DGMOSFETs for modeling purposes. Solid-State Electronics, 2013, 79, 92-97.	0.8	2
241	In Situ Characterization of Bias Instability in Bare SOI Wafers by Pseudo-MOSFET Technique. IEEE Transactions on Device and Materials Reliability, 2014, 14, 878-883.	1.5	2
242	Direct Characterization of Impact Ionization Current in Silicon-on-Insulator Body-Contacted MOSFETs. ECS Transactions, 2015, 66, 93-99.	0.3	2
243	Effects of dietary choline availability on latent inhibition of flavor aversion learning. Nutritional Neuroscience, 2015, 18, 275-280.	1.5	2
244	Strain effects on effective masses for MoS ₂ monolayers. Journal of Physics: Conference Series, 2015, 609, 012008.	0.3	2
245	Role of the gate in ballistic nanowire SOI MOSFETs. Solid-State Electronics, 2015, 112, 24-28.	0.8	2
246	Response to "Comment on "Assessment of field-induced quantum confinement in heterogate germanium electron-hole bilayer tunnel field-effect transistor" [Appl. Phys. Lett. 106, 026102 (2015)]. Applied Physics Letters, 2015, 106, 026103.	1.5	2
247	Band-to-band tunneling distance analysis in the heterogate electron-hole bilayer tunnel field-effect transistor. Journal of Applied Physics, 2016, 119, .	1.1	2
248	Comment on "Optimization of a Pocketed Dual-Metal-Gate TFET by Means of TCAD Simulations Accounting for Quantization-Induced Bandgap Widening" IEEE Transactions on Electron Devices, 2016, 63, 5077-5078.	1.6	2
249	Confinement orientation effects in S/D tunneling. , 2016, , .		2
250	Multi-subband ensemble Monte Carlo study of band-to-band tunneling in silicon-based TFETs. , 2016, , .		2
251	Active charge collection strategy for radiation environment at device level. , 2016, , .		2
252	Impact of non uniform strain configuration on transport properties for FD14+ devices. Solid-State Electronics, 2016, 115, 232-236.	0.8	2

#	ARTICLE	IF	CITATIONS
253	The mystery of the Z2-FET 1T-DRAM memory. , 2017, , .		2
254	Simulation study on Z2FET scalability, process optimization and their impact on performance. , 2018, , .		2
255	Z ² -FET memory matrix in 28 nm FDSOI technology. , 2018, , .		2
256	Experimental Characterization of the Random Telegraph Noise Signature in MOSFETs Under the Influence of Magnetic Fields. IEEE Electron Device Letters, 2018, 39, 1054-1057.	2.2	2
257	Characteristics of band modulation FET on sub 10 nm SOI. Japanese Journal of Applied Physics, 2019, 58, SBBB07.	0.8	2
258	A thorough study of Si nanowire FETs with 3D Multi-Subband Ensemble Monte Carlo simulations. Solid-State Electronics, 2019, 159, 19-25.	0.8	2
259	Memory Operation of Z ² -FET Without Selector at High Temperature. IEEE Journal of the Electron Devices Society, 2021, 9, 658-662.	1.2	2
260	Improved Retention Characteristics of Z2-FET Employing Half Back-Gate Control. IEEE Transactions on Electron Devices, 2021, 68, 1041-1044.	1.6	2
261	Performance and reliability in back-gated CVD-grown MoS2 devices. Solid-State Electronics, 2021, 186, 108173.	0.8	2
262	Systematic Characterization of Random Telegraph Noise and Its Dependence with Magnetic Fields in MOSFET Devices. , 2020, , 135-174.		2
263	Multi-Subband Ensemble Monte Carlo Simulator for Nanodevices in the End of the Roadmap. Lecture Notes in Computer Science, 2020, , 438-445.	1.0	2
264	Improved inter-device variability in graphene liquid gate sensors by laser treatment. Solid-State Electronics, 2022, 192, 108259.	0.8	2
265	A detailed simulation study of the performance of -silicon carbide MOSFETs and a comparison with their silicon counterparts. Semiconductor Science and Technology, 1997, 12, 655-661.	1.0	1
266	Electron mobility in quantized $\hat{1}^2$ -SiC inversion layers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1631.	1.6	1
267	A $\hat{1}^2$ -SiC MOSFET Monte Carlo Simulator Including Inversion Layer Quantization. VLSI Design, 1998, 8, 257-260.	0.5	1
268	A computational study of the strained-Si MOSFET: a possible alternative for the next century electronics industry. Computer Physics Communications, 1999, 121-122, 547-549.	3.0	1
269	Low temperature transport properties of thin SOI MOSFETs. Superlattices and Microstructures, 2003, 34, 341-345.	1.4	1
270	A new remote Coulomb scattering model for ultrathin oxide MOSFETs. , 2003, , .		1

#	ARTICLE	IF	CITATIONS
271	Accurate deterministic numerical simulation of p-n junctions. , 2004, , .		1
272	DGSOI devices operated as velocity modulation transistors. , 0, , .		1
273	Retinal Implant Electrode Arrays with 10V SOI CMOS Circuitry. , 0, , .		1
274	Double gate silicon-on-insulator transistors: n/sup +/-n/sup +/- gate versus n/sup +/-p/sup +/- gate configuration. , 0, , .		1
275	Study of the Corner Effects on Pi-Gate SOI MOSFETs. , 2007, , .		1
276	Charge transport in nanoscaled silicon-on-insulator devices. , 2007, , .		1
277	Ballisticity at very low drain bias in DG SOI Nano-MOSFETs. , 2007, , .		1
278	Geometric Magnetoresistance and Mobility Behavior in Single-Gate and Double-Gate SOI Devices. SOI Conference, Proceedings of the IEEE International, 2007, , .	0.0	1
279	A revisited pseudo-MOSFET model for ultrathin SOI films. , 2008, , .		1
280	A In-depth Simulation Study of CMOS Inverters Based on the Novel Surrounding Gate Transistors. , 2008, , .		1
281	Effect of Arbitrary Orientation and Strain on Surrounding Gate Transistors. , 2009, , .		1
282	The influence of orientation and strain on the transport properties of SOI trigate nMOSFETs. , 2009, , .		1
283	Origins of universal mobility violation in SOI MOSFETs. , 2010, , .		1
284	Analytical drain current model reproducing advanced transport models in nanoscale double-gate (DG) MOSFETs. , 2011, , .		1
285	Multibranch mobility characterization: Evidence of carrier mobility enhancement by back-gate biasing in FD-SOI MOSFET. , 2012, , .		1
286	Innovative capacitorless SOI DRAMs. , 2012, , .		1
287	Experimental demonstration of A2RAM memory cell on SOI. , 2012, , .		1
288	Influence of the back-gate bias on the electron mobility of trigate MOSFETs. , 2013, , .		1

#	ARTICLE	IF	CITATIONS
289	Analytical drain current model using temperature dependence model in nanoscale Double-Gate (DG) MOSFETs. , 2013, , .		1
290	Direct point-contact characterization of Bias instability on bare SOI wafers. , 2013, , .		1
291	Notice of Removal: Fabrication and validation of A2RAM memory cells on SOI and bulk substrates - Withdrawn. , 2013, , .		1
292	Improving subthreshold MSB-EMC simulations by dynamic particle weighting. , 2013, , .		1
293	Implicit versus explicit momentum relaxation time solution for semiconductor nanowires. Journal of Applied Physics, 2015, 118, 024504.	1.1	1
294	Electrical characterization of Random Telegraph Noise in back-biased Ultrathin Silicon-On-Insulator MOSFETs. , 2016, , .		1
295	Characterization of semiconductor structures using scanning microwave microscopy technique. , 2017, , .		1
296	Three-dimensional multi-subband simulation of scaled FinFETs. , 2017, , .		1
297	Scaling FDSOI technology down to 7 nm " A physical modeling study based on 3D phase-space subband boltzmann transport. , 2018, , .		1
298	Temperature and Gate Leakage Influence on the Z2-FET Memory Operation. , 2019, , .		1
299	Self-Consistent Enhanced S/D Tunneling Implementation in a 2D MS-EMC Nanodevice Simulator. Micromachines, 2021, 12, 601.	1.4	1
300	CVD-grown back-gated MoS2 transistors. , 2020, , .		1
301	Strained Si/SiGe Heterostructures at Low Temperatures. A Monte Carlo Study. European Physical Journal Special Topics, 1996, 06, C3-87-C3-92.	0.2	1
302	Monte Carlo Simulation of a Submicron MOSFET Including Inversion Layer Quantization. VLSI Design, 1998, 6, 287-290.	0.5	1
303	Low temperature mobility improvement in high-mobility strained-Si/Si _{1-x} Ge _x multilayer MOSFETs. European Physical Journal Special Topics, 1998, 08, Pr3-57-Pr3-60.	0.2	1
304	Semi-empirical model of electron mobility in MOSFETs in strong inversion regime. IET Circuits, Devices and Systems, 1996, 143, 202.	0.6	0
305	Two-dimensional drift-diffusion simulation of superficial strained-Si/Si _{1-x} Ge _x channel metal-oxide-semiconductor field-effect transistors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 1538.	1.6	0
306	Development of a Method for Determining the Dependence of the Electron Mobility on the Longitudinal-Electric Field in MOSFETs. VLSI Design, 1998, 8, 261-264.	0.5	0

#	ARTICLE	IF	CITATIONS
307	Monte Carlo Simulation of Non-Local Transport Effects in Strained Si on Relaxed Si _{1-x} Ge _x Heterostructures. VLSI Design, 1998, 8, 253-256.	0.5	0
308	Comparison Between Non-Equilibrium Green's Function and Monte Carlo Simulations for Transport in a Silicon Quantum Wire Structure. Journal of Computational Electronics, 2003, 2, 335-339.	1.3	0
309	Double gate silicon-on-insulator transistors: n ⁺ /n ⁺ gate versus n ⁺ /p ⁺ gate configuration. , 0, , .		0
310	Monte Carlo simulation of electron velocity overshoot in DGSOI MOSFETs. , 2004, , .		0
311	Monte Carlo Simulation of Electron Velocity Overshoot in DGSOI MOSFETs. Journal of Computational Electronics, 2004, 3, 295-298.	1.3	0
312	Electron transport in silicon inversion slabs of nanometric thickness. , 2005, , .		0
313	Title is missing!. Solid-State Electronics, 2005, 49, 1453.	0.8	0
314	SPICE BSIMSOI enhancement to account for velocity overshoot effects. , 0, , .		0
315	Monte Carlo simulation of velocity modulation transistors. , 0, , .		0
316	Confined acoustic phonons in ultrathin SOI layers. Journal of Computational Electronics, 2006, 5, 199-203.	1.3	0
317	Characterization of electron transport at high fields in silicon-on-insulator devices: a Monte Carlo study. Semiconductor Science and Technology, 2006, 21, 81-86.	1.0	0
318	A Comprehensive Study of the Corner Effects in Pi-Gate SOI MOSFETs. ECS Transactions, 2007, 6, 363-368.	0.3	0
319	Quantum corrected EMC simulation of ultrashort DGSOI devices. Ballistic vs. Diffusive regime. , 2007, , .		0
320	Enhanced electron transport by carrier overshoot in ultrascaled Double Gate MOSFETs. , 2008, , .		0
321	Accurate Simulation of the Electron Density of Surrounding Gate Transistors. , 2009, , .		0
322	Using Grid Infrastructures for a Stationary DGSOI Monte Carlo Simulation. , 2009, , .		0
323	A new inversion charge centroid model for surrounding gate transistors with HfO ₂ as gate insulator. , 2009, , .		0
324	Simulation of Hole Mobility in DGSOI Transistors. ECS Transactions, 2009, 19, 235-240.	0.3	0

#	ARTICLE	IF	CITATIONS
325	Ultrathin Body Effects in Multiple Gate SOI Transistors. ECS Transactions, 2009, 25, 91-98.	0.3	0
326	Characterization, modelling and simulation of Sub-45nm SOI devices. , 2009, , .		0
327	Non-metallic effects in silicided gate MOSFETs. Solid-State Electronics, 2009, 53, 1313-1317.	0.8	0
328	Quantization effects in silicided and metal gate MOSFETs. , 2009, , .		0
329	Quantum-Monte Carlo simulation of ultra-short DGSOI devices: A Multi-Subband approach. , 2009, , .		0
330	Comparison of semiclassical transport formulations including quantum corrections for advanced devices with High-K gate stacks. , 2010, , .		0
331	Effects of deviations in the cross-section of square nanowires. , 2010, , .		0
332	Multi-Subband Monte Carlo simulation of bulk MOSFETs for the 32nm-node and beyond. , 2010, , .		0
333	On the effective mass of holes in inversion layers. , 2011, , .		0
334	Ultrathin n-Channel and p-Channel SOI MOSFETs. Engineering Materials, 2011, , 169-185.	0.3	0
335	New Capacitorless Dynamic Memory Compatible with SOI and Bulk CMOS. ECS Transactions, 2011, 35, 195-200.	0.3	0
336	ADVANCED CONCEPTS FOR FLOATING-BODY MEMORIES. International Journal of High Speed Electronics and Systems, 2012, 21, 1250002.	0.3	0
337	3D Trigate 1T-DRAM Memory Cell for 2x nm Nodes. , 2012, , .		0
338	Combined effect of mechanical stressors and channel orientation on mobility in FDSOI n and p MOSFETs. , 2012, , .		0
339	Effect of interfacial states on the technological variability of trigate MOSFETs. , 2012, , .		0
340	Ab initio validation of continuum models for Si/SiO ₂ /Si interfaces. , 2013, , .		0
341	Effective Capacitance Area for Pseudo-MOSFET Characterization of Bare SOI Wafers by Split-C(V) Measurements. ECS Journal of Solid State Science and Technology, 2013, 2, P529-P533.	0.9	0
342	Non-parabolicity in Si-(110) nMOSFETs: Analytic and numerical results for the two-band k ² model. , 2013, , .		0

#	ARTICLE	IF	CITATIONS
361	New material design of fast switching phase change memory as the benchmark for FD-SOI devices. , 2019, , .		0
362	Impact of Effective Mass on Transport Properties and Direct Source-to-Drain Tunneling in Ultrascaled Double Gate Devices: a 2D Multi-Subband Ensemble Monte Carlo study. , 2019, , .		0
363	Monte-Carlo SSA Analysis of the NAO Index. , 2001, , 309-320.		0
364	Quantum-Corrected Monte Carlo Simulation of Double Gate Silicon on Insulator Transistors. Journal of Computational and Theoretical Nanoscience, 2008, 5, 1046-1057.	0.4	0
365	Low-Temperature Modelling of Electron-Velocity-Overshoot Effects on 70-250 nm Gate-Length MOSFETs. European Physical Journal Special Topics, 1996, 06, C3-13-C3-18.	0.2	0
366	Simulation of Electron Mobility in Ultrathin Fully Depleted Single Gate SOI MOSFETs. , 1998, , 113-116.		0
367	I-V and small signal parameters modelling of ultrasubmicron MOSFETs including the significant electron-velocity overshoot effects, which are enhanced at low temperature. European Physical Journal Special Topics, 1998, 08, Pr3-21-Pr3-24.	0.2	0
368	Efficient Implementation of S/D tunneling in 2D MS-EMC of Nanoelectronic Devices Including the Thickness Dependent Effective Mass. , 2020, , .		0
369	Techniques for Statistical Enhancement in a 2D Multi-subband Ensemble Monte Carlo Nanodevice Simulator. Lecture Notes in Computer Science, 2020, , 411-419.	1.0	0
370	Analysis of the Reformulated Source to Drain Tunneling Probability for Improving the Accuracy of a Multisubband Ensemble Monte Carlo Simulator. Micromachines, 2022, 13, 533.	1.4	0
371	Electron Transport in Silicon-on-Insulator Nanodevices. NATO Science for Peace and Security Series B: Physics and Biophysics, 0, , 303-322.	0.2	0
372	Influence of Punch Trough Stop Layer and Well Depths on the Robustness of Bulk FinFETs to Heavy Ions Impact. IEEE Access, 2022, 10, 47169-47178.	2.6	0